



Self-aligned Double Patterning Layout Decomposition with Complementary E-Beam Lithography

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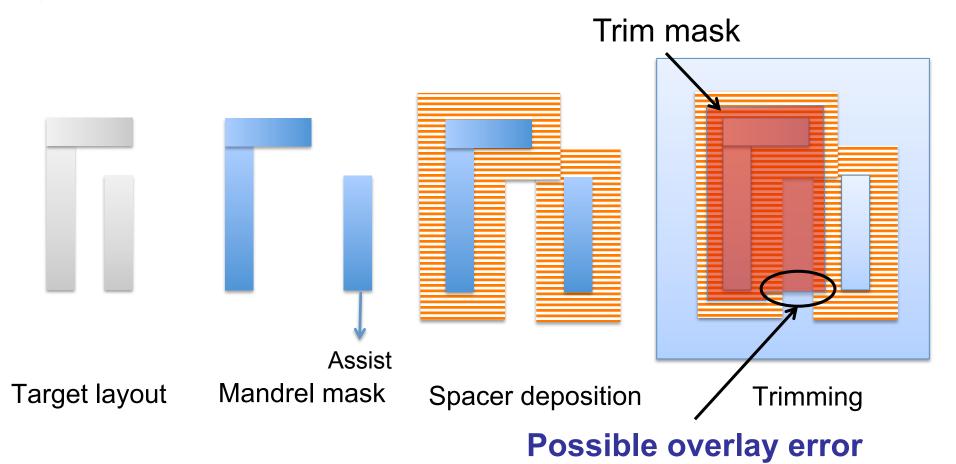
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Outline

- Motivation & Problem Formulation
- Proposed Algorithms
 - Post Processing Based Layout Decomposition
 - Simultaneous SADP+EBL Optimization
- Experimental Results
- Conclusion

Self-Aligned Double Patterning (SADP)

- Promising double patterning technique for sub-22nm nodes
- Trim mask can be used to generate cuts
- Issue: Overlay problem caused on some trimming boundaries



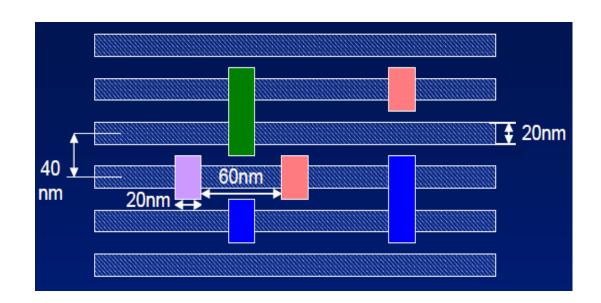
E-Beam Lithography (EBL)

- Maskless lithography
 - High Resolution (sub-10nm)
- Issue: Low throughput
- Constraint: Variable-shaped (rectangular) beam system

Each e-beam cut is a rectangular **Electrical Gun Shaping Aperture** 2nd Aperture Wafer

SADP & E-beam Hybrid?

SADP with multiple cut masks or e-beam cuts



11nm node

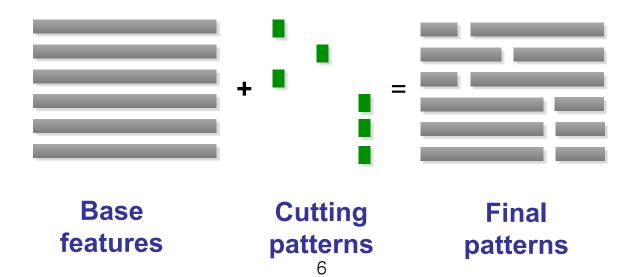
193nm immersion
1 base mask + 4 cut masks

Complementary Lithography

1 base mask + E-beam

Complementary/Hybrid Lithography

- Different lithography techniques work together
 - › Base features: Optical lithography or SADP
 - » Low cost, low resolution
 - Cutting technique: high-resolution MPL/EUVL/EBL/DSA
 - » High cost, high resolution
 - Tradeoff b/t Printing Quality and Manufacturing Cost
- ◆ This work: SADP + EBL



Related Works

- Complementary lithography
 - Y. Borodovsky, Maskless Lithography and Multibeam Mask Writer Workshop, 2010]
- SADP with line cutting for 1D layout
 - K. Oyama et al., SPIE 2010]
- SADP with EBL line cutting for 1D layout
 - D. Lam et al., SPIE 2011], [Y. Du et al., ASPDAC 2012]
- SADP layout decompositions for 2D layouts
 - [Ban+, DAC'11], [H. Zhang+, DAC'11], [Xiao+, TCAD13]

Problem Formulation

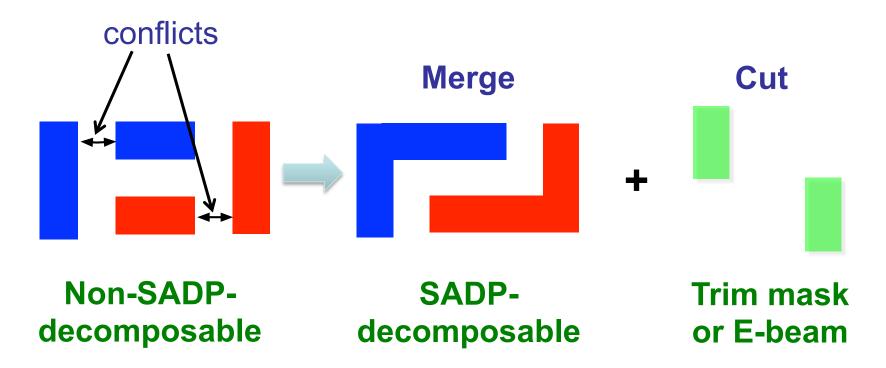
- Given
 - General 2D layouts
 - Minimum pattern spacing on a single mask
- Objective: Perform layout decomposition with SADP+EBL
 - No min-spacing conflict for mandrel/trim mask
 - Minimize overlay error caused by trim mask
 - Minimize e-beam shots

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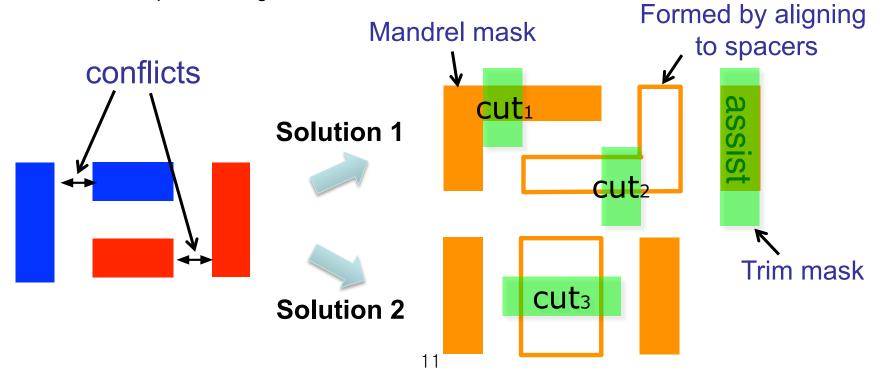
Dealing with SADP Conflicts

- Merge&Cut (M&C) technique
 - Step1: Merge conflicting patterns
 - Step2: Cut unwanted parts by trim mask or e-beams



Merge & Cut (M&C) Technique

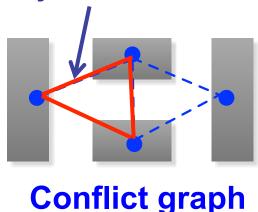
- May have multiple solution candidates
- Cut cost
 - Cost of trim mask cut = α * Length of cutting boundary
 - » Penalty to minimize overlay error
 - Cost of e-beam cut = β * Number of shots required
 - » Set β much larger than α to minimize e-beam shot counts

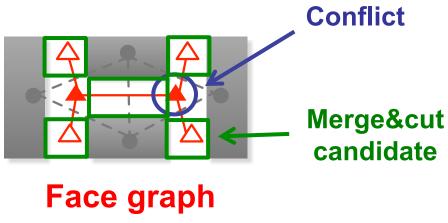


Finding M&C Solutions

- Objective: solve all conflicts with minimum cost
- Matching-based algorithm
 - Step1: Conflict Graph construction
 - Step2: Dual Face Graph construction
 - » Conflict node: an odd face on the conflict graph
 - » M&C node: a M&C candidate to solve a conflict
 - » Edge: b/t a conflict node and its M&C solution candidates

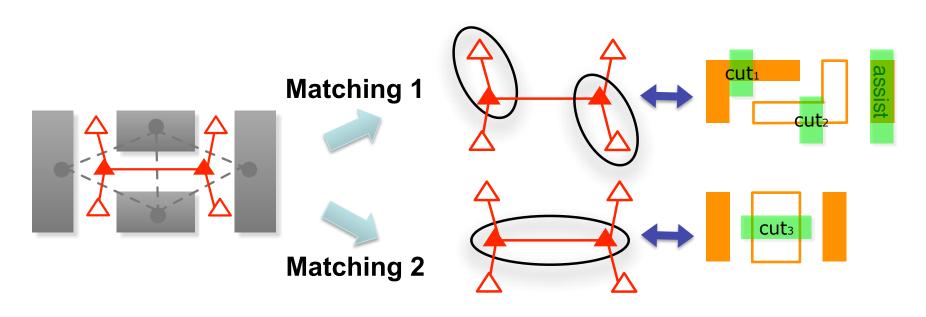
Odd cycle = Conflict



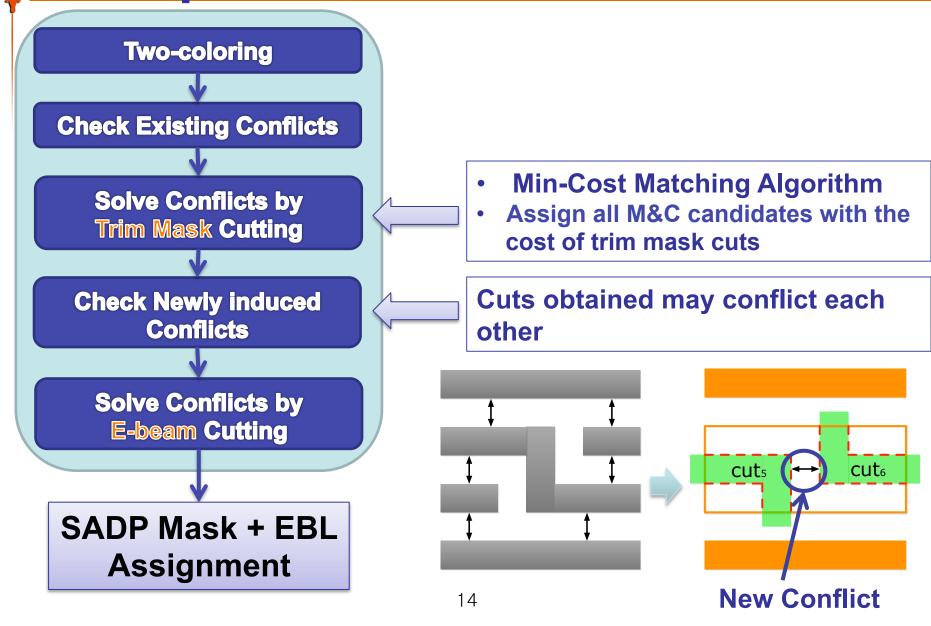


Finding M&C Solutions (cont)

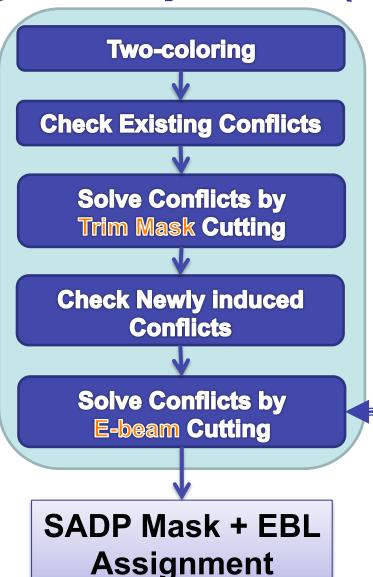
- Matching-based algorithm
 - Step 3: Apply min-cost matching algorithm on face graph
 - » Edge = conflict solved by a M&C candidate
 - » Each conflict node only needs to be covered once
 - → Matching solution = Selection of M&C candidates that can solve conflicts with the minimum cost



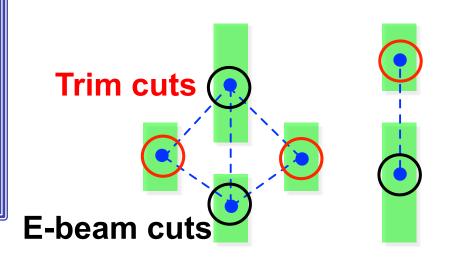
Method 1: Post Processing Based Layout Decomposition



Method 1: Post Processing Based Layout Decomposition (cont)

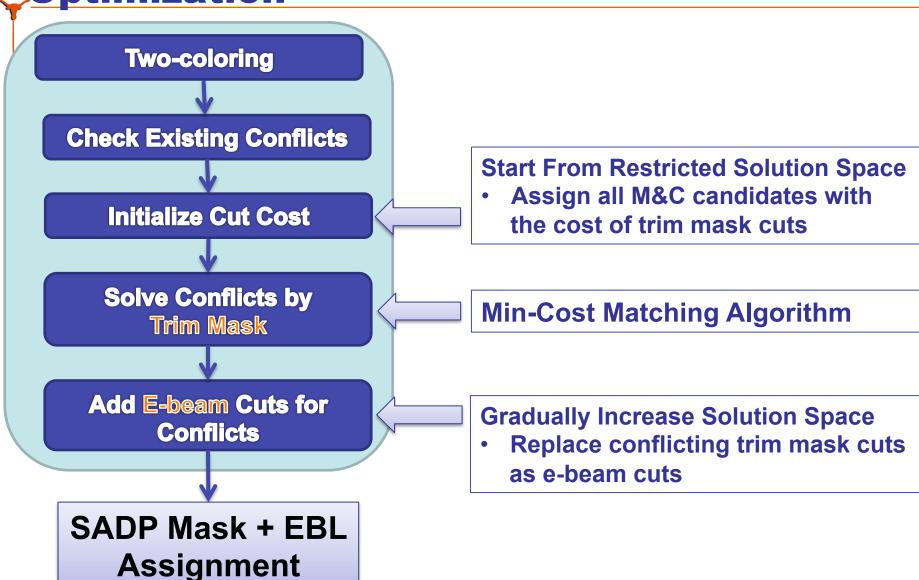


- Construct conflict graph for cuts
- Find trim cuts by Maximal Independent Set algorithm
- Assign the rest of cuts as e-beams

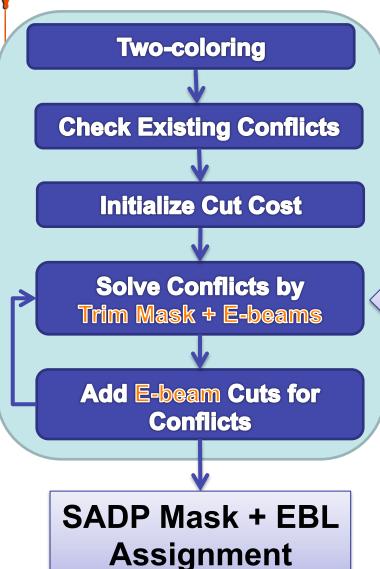


E-beam only considered at the last stage (Greedy)

Method 2: Simultaneous SADP+EBL Optimization



Method 2: Simultaneous SADP+EBL Optimization (cont)

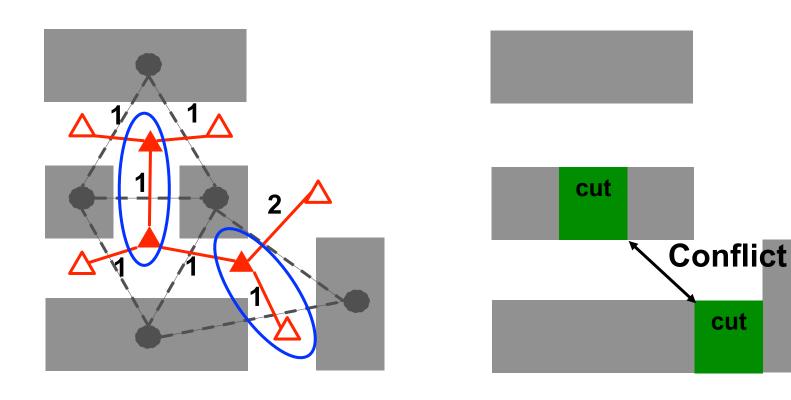


Min-Cost Matching Algorithm

- Similar to the previous iteration, but now we have two types of cuts
- E-beam Cut Cost >> Trim Cut Cost

Simultaneously selecting trim mask cuts and e-beam cuts

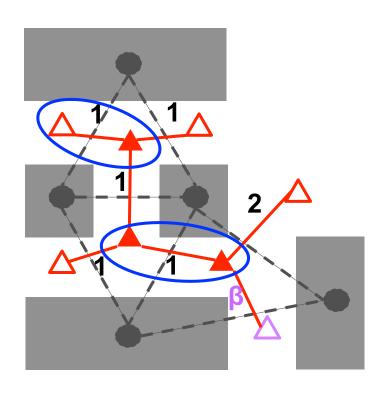
Initialize cost of all cuts based on trim mask cutting length



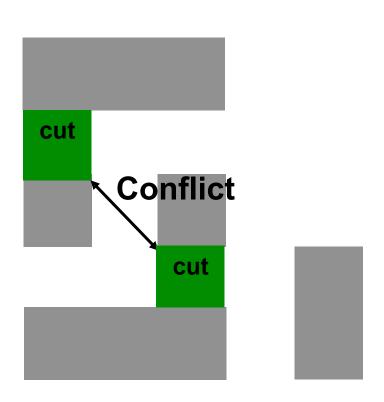
Iter. 1 Matching solution

Check trim cuts

Update one conflicting cut as EBL cut (cost = β)

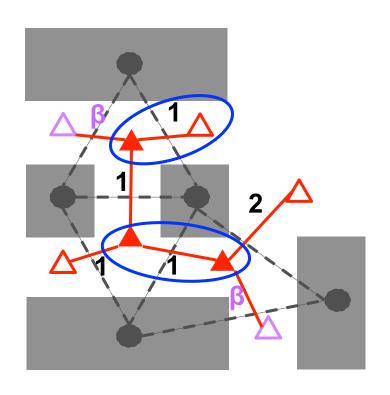


Iter. 2 Matching solution

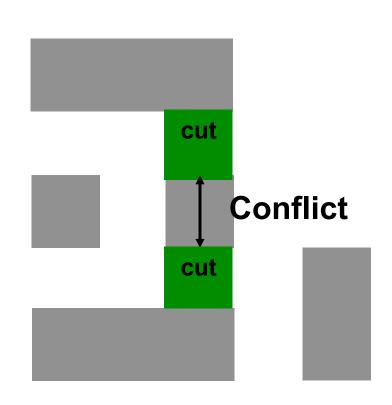


Check trim cuts

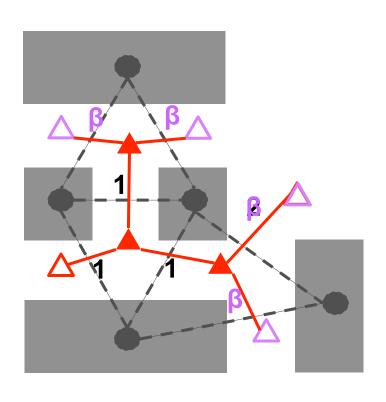
Update cost



Iter. 3 Matching solution

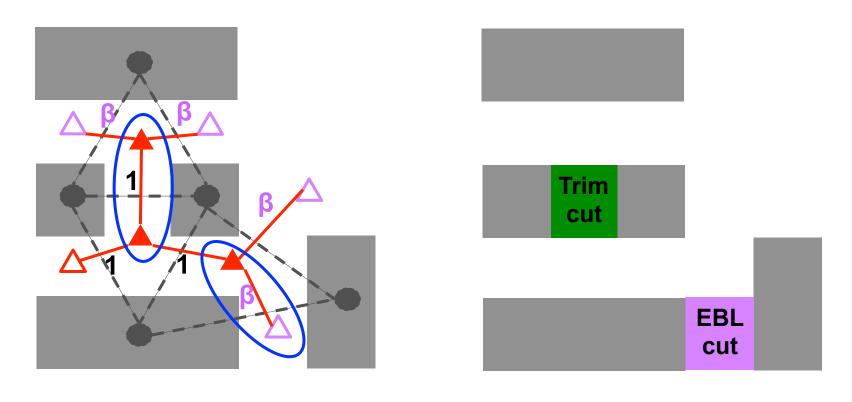


Check trim cuts



Keep going...

Continue iterations until no conflict in cuts



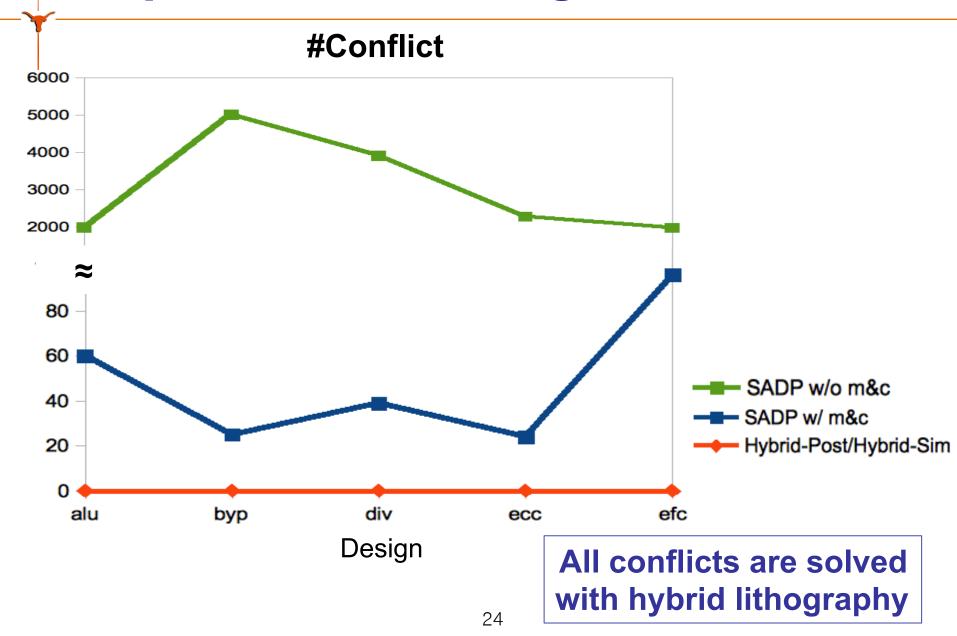
Final matching solution

Final cut assignment

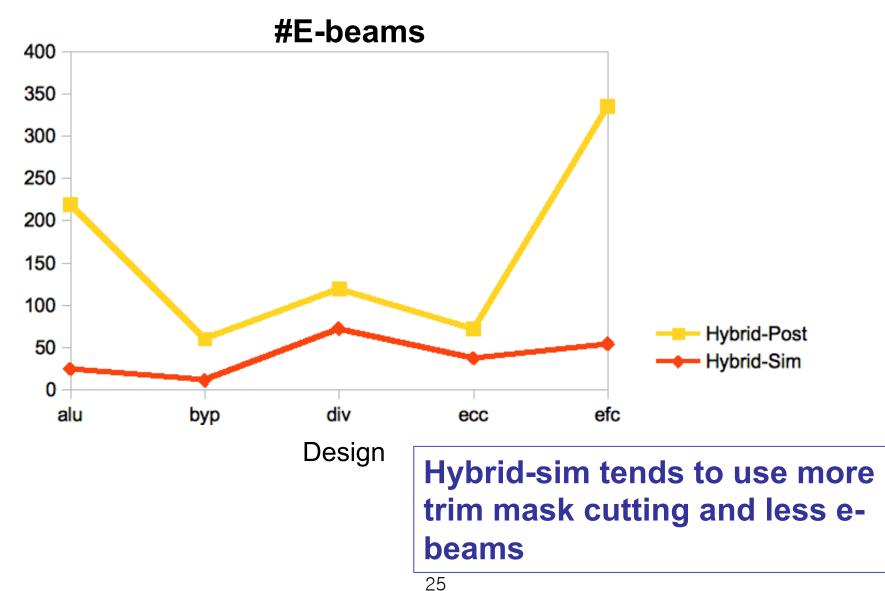
Experiment Settings

- Benchmarks
 - OpenSPARC T1 designs
 - Scaled down to 22nm
- Comparison methods
 - SADP w/o merge&cut
 - SADP w/ merge&cut
 - Hybrid-post: post-processing based decomposition
 - Hybrid-sim: simultaneous SADP+EBL decomposition

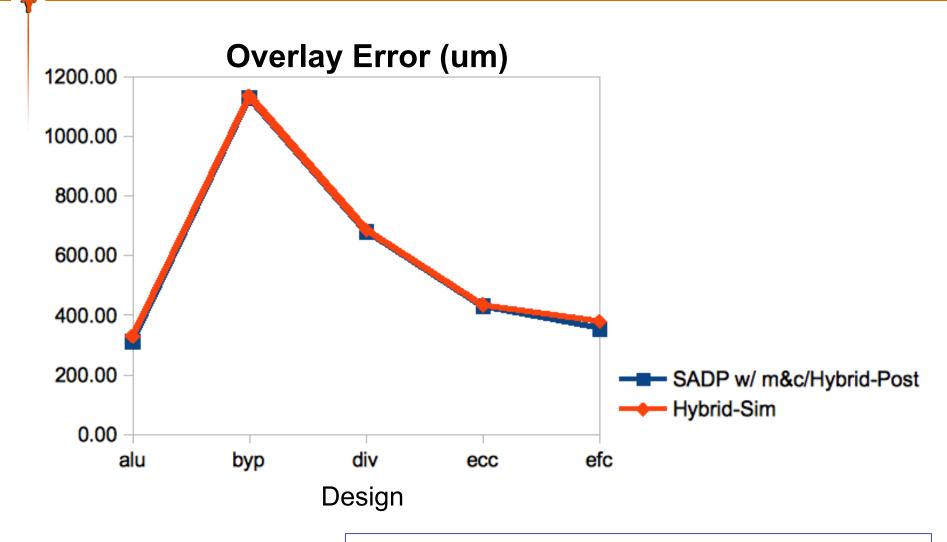
Comparison of Remaining Conflicts



Comparison of E-beam Utilization



Comparison of Overlay Error



Overlay increase by Hybrid-sim < 3%

Conclusion

- Complementary lithography enables high quality layout with less mask manufacturing cost
- Merge & cut technique to reduces conflicts
- Simultaneous SADP layout decomposition and E-beam assignment performed effectively to minimize
 - Conflict
 - SADP overlay due to trim mask
 - E-beam shot counts

Thank You